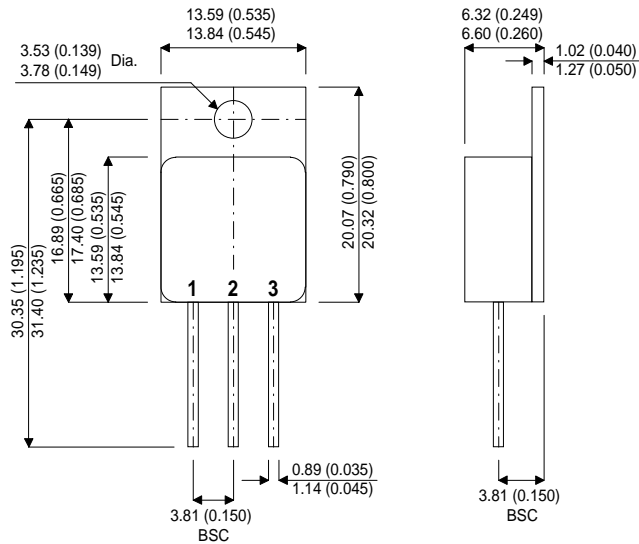


**MECHANICAL DATA**

Dimensions in mm



**DUAL SCHOTTKY  
BARRIER DIODE IN  
TO254 METAL PACKAGE  
FOR HI-REL APPLICATIONS**

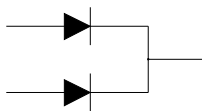
**FEATURES**

- HERMETIC TO254 METAL PACKAGE
- ISOLATED CASE
- SCREENING OPTIONS AVAILABLE
- OUTPUT CURRENT 35A
- LOW  $V_F$
- LOW LEAKAGE

**TO254 METAL PACKAGE**

Common Cathode

**SB35-45M**  
**SB35-40M**



1 = A<sub>1</sub> Anode 1  
 2 = K Cathode  
 3 = A<sub>2</sub> Anode 2

**ABSOLUTE MAXIMUM RATINGS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

	SB35-40M	SB35-45M
$V_{RRM}$ Peak Repetitive Reverse Voltage	40V	45V
$V_{RSM}$ Peak Non-Repetitive Reverse Voltage	40V	45V
$V_R$ Continuous Reverse Voltage	40V	45V
$I_O$ Output Current	35A	
$I_{FSM}$ Peak Non-Repetitive Surge Current (50Hz)	245A	
$T_{STG}$ Storage Temperature Range	-55°C to 150°C	
$T_J$ Maximum Operating Junction Temperature	150°C/W	

**ELECTRICAL CHARACTERISTICS** (Per Diode)( $T_{CASE} = 25^{\circ}C$  unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_F$ Forward Voltage	$I_F = 5A$			0.49	V
	$I_F = 25A$ $T_J = 125^{\circ}C$			0.85	
	$I_F = 50A$			1.25	
$I_R$ Reverse Current	$V_R = V_{RRM}$ $T_J = 25^{\circ}C$			5	mA
	$V_R = V_{RRM}$ $T_J = 125^{\circ}C$			45	
$C_d$ Junction Capacitance	$V_R = 5 V$ $f = 1 MHz$		3000		pF

Pulse test  $t_p=300\mu s$   $\delta \leq 2\%$

Parameter		Unit
$R_{TH(j-a)}$ Maximum Thermal Resistance Junction To Case	both diodes 1.4 per diode 2.3	$^{\circ}C/W$
$R_{TH(j-c)}$ Maximum Thermal Resistance Junction To Case	1.3	$^{\circ}C/W$